

## Electrical control of single hole spins in nanowire quantum dots

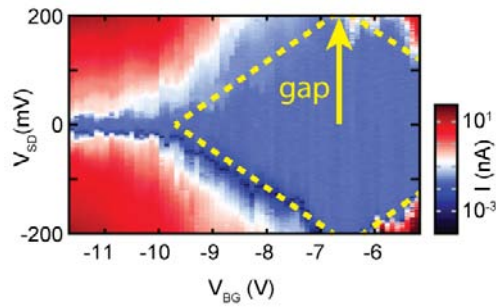
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## 1. Bandgap of InSb nanowires

We extract the bandgap of our InSb nanowires using the basic device described in Fig. 1 of the main text. On the left side of Fig. S1, the Fermi level is in the valence band, resulting in a finite current away from zero bias. At less negative  $V_{BG}$ , the Fermi level is inside the bandgap and the current is suppressed. On the right side of the figure, at even less negative  $V_{BG}$ , current is restored as the Fermi level moves into the conduction band. We extract the bandgap,  $\sim 0.2$  eV, from the extent of the non-conducting region, as shown by the arrow in Fig. S1. This value is in agreement with the gap of bulk InSb ( $\sim 0.17$  eV at room temperature and  $\sim 0.23$  eV at low temperatures [1]), and is confirmed by similar measurements in one other InSb nanowire device.



*Fig. S1: Current through an InSb nanowire as a function of  $V_{SD}$  and  $V_{BG}$ .*















